



NPN General Purpose Amplifier

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19. See PN2222A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	75	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	1.0	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		TN2219A	
P _D	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	W/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W

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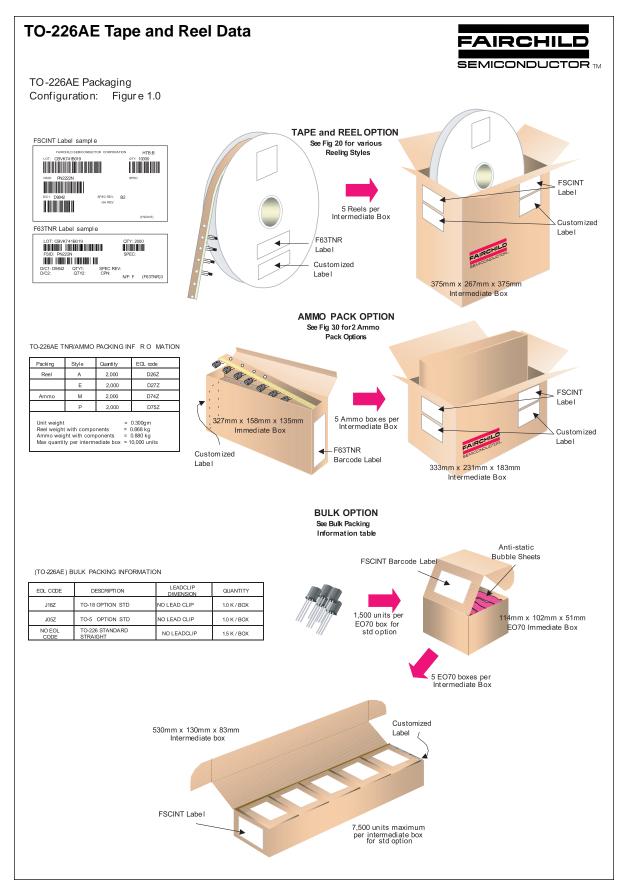
¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

NPN General Purpose Amplifier (continued)

Parameter	Test Conditions	Min	Max	Units
RACTERISTICS				
Collector-Emitter Breakdown Voltage*	I _C = 10 mA, I _B = 0	40		V
, and the second		75		V
•	•			V
•	, -	0.0	10	nA
			_	nA
Collector Cutori Current			_	μA
Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$		10	nΑ
Base Cutoff Current			20	nA
ACTERISTICS	1 - 0.1 mA \/ - 10 \/	25		
DC Current Gain				
	$I_{\rm C} = 10 \text{mA}, V_{\rm CE} = 10 \text{V}$	75		
	$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$	100	300	
	$I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$	50		
		40	0.0	
Collector-Emitter Saturation Voltage*				V
Base-Emitter Saturation Voltage*		0.6	1.2	V
	$I_C = 500 \text{ mA}, I_B = 5.0 \text{ mA}$		2.0	V
GNAL CHARACTERISTICS	V 40 V 1 0 (400 III-		0.0	
· · ·				pF
Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_{C} = 0, f = 100 \text{ kHz}$		25	
-				pF
Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$	50	300	pr
	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}, f = 1.0 \text{ kHz}$	50 75	375	
Small-Signal Current Gain Collector Base Time Constant Noise Figure	, ,			pS dB
	Base Cutoff Current ACTERISTICS DC Current Gain Collector-Emitter Saturation Voltage* Base-Emitter Saturation Voltage*			

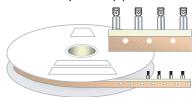
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%



TO-226AE Tape and Reel Data, continued

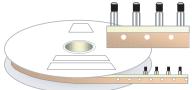
TO-226AE Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A" D26Z, D70Z (s/h)

Machine Option "E"(J)



Style "E" D27Z, D71Z (s/h)

TO-226AE Radial Ammo Packaging

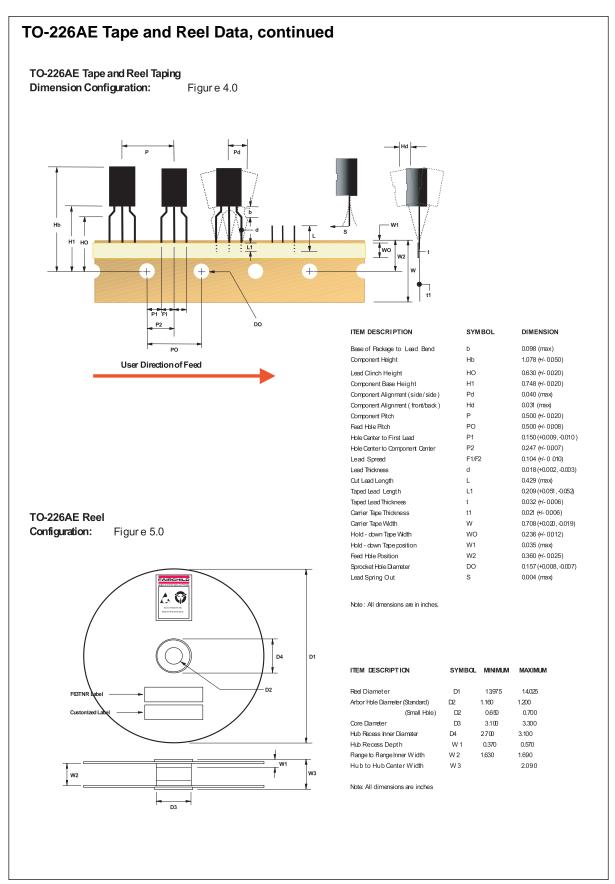
Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM FIRST WIRE OFF IS EMITTER (ON PKG. 92) ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM



FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

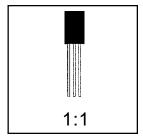


TO-226AE Package Dimensions



TO-226AE (FS PKG Code 95, 99)

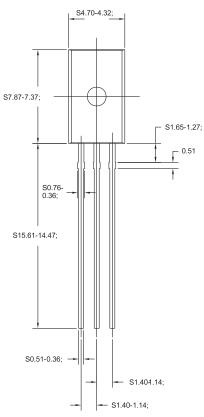


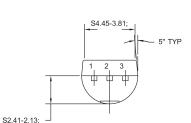


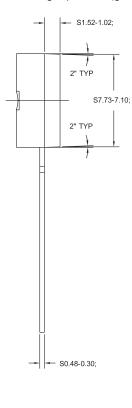
Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.300









For leadformed option ordering, refer to Tape & Reel data information.

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